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~~said [a] channel region having a first doped region of opposite conductivity type and a second doped region underlying the first doped region of said opposite conductivity type, said second doped region having a lower dopant concentration than said first doped region, said second doped region being the primary conduction channel between said source and said drain[; a source adjacent to the channel; and a drain adjacent to the channel]~~

Cancel claim 2 without prejudice.

Claim 3, line 1, change "2" to --1--.

Amend claim 7 as follows:

7. (Amended) A semiconductor device comprising:

Subc2 B.2
a plurality of field effect transistors, at least one of the field effect transistors having a channel [comprising a subsurface doped layer], [the field effect transistor further having] a source of first conductivity type adjacent to the channel, a drain of said first conductivity type adjacent to the channel and spaced from said source and a gate overlying the channel;

said channel comprising a first doped region of opposite conductivity type and a second doped region underlying the first doped region of said opposite conductivity type, said second doped region having a lower dopant concentration than said first doped region, said second doped region being the primary conduction channel between said source and said drain.